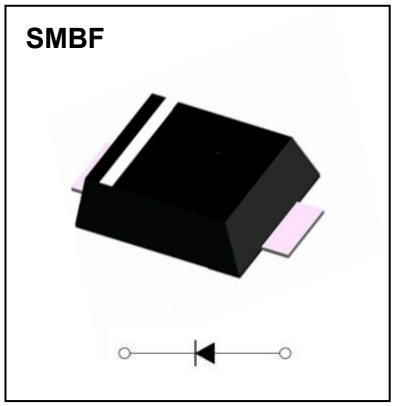
SMBF Plastic-Encapsulate Diodes

RS4ABF THRU RS4MBF **Fast Recovery Rectifier Diodes**

Features

- $I_{F(AV)}$ 4A
- V_{RRM} 50V-1000V
- High surge current capability
- Polarity: Color band denotes cathode



Applications

- Rectifier

Marking

- RS4XBF

  X：From A To M

Limiting Values(Absolute Maximum Rating)

Item	Symbol	Unit	Test Conditions	RS4						
				ABF	BBF	DBF	GBF	JBF	KBF	MBF
Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
Maximum RMS Voltage	V_{RMS}	V		35	70	140	280	420	560	700
Average Forward Current	$I_{F(AV)}$	A	60Hz Half-sine wave，Resistance load，TL= 100 ℃	4.0						
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz Half-sine wave，1 cycle，Ta=25℃	120						
Junction Temperature	T_J	℃		-55 ~ +150						
Storage Temperature	T_{STG}	℃		-55 ~ +150						

Electrical Characteristics (T=25℃ Unless otherwise specified）

Item	Symbol	Unit	Test Condition		RS4						
					ABF	BBF	DBF	GBF	JBF	KBF	MBF
Peak Forward Voltage	V_F	V	I_F=4.0A		1.3						
Peak Reverse Current	I_{RRM1}	μA	$V_{RM}=V_{RRM}$	Ta =25℃	5						
	I_{RRM2}			Ta =125℃	500						
Thermal Resistance(Typical)	$R_{\theta J-A}$	℃/W	Between junction and ambient		78						
Typical junction capactiance per diode	C_J	pF	Measured at 1.0MHz and applied reverse voltage of 4.0 volts.		68						
Maximum reverse recovery time	t_{rr}	ns	I_F=0.5A,I_R=1.0A,I_{rr}=0.25A		150				250	500	

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

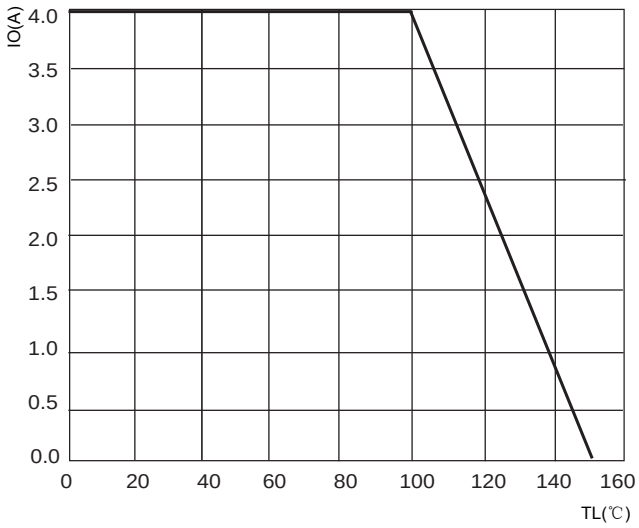


FIG2:Surge Forward Current Capadility

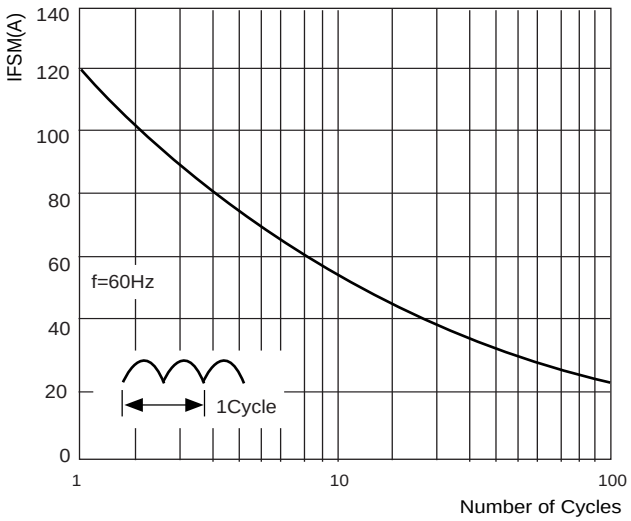


FIG.3: TYPICAL FORWARD CHARACTERISTICS

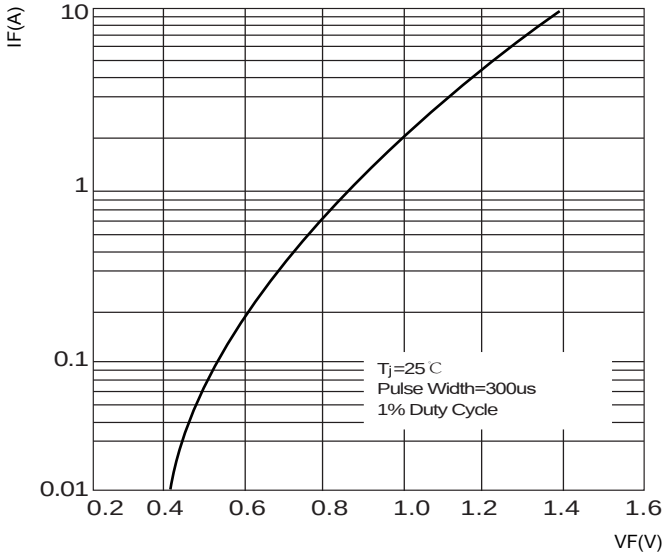


FIG.4 ：TYPICAL REVERSE CHARACTERISTICS

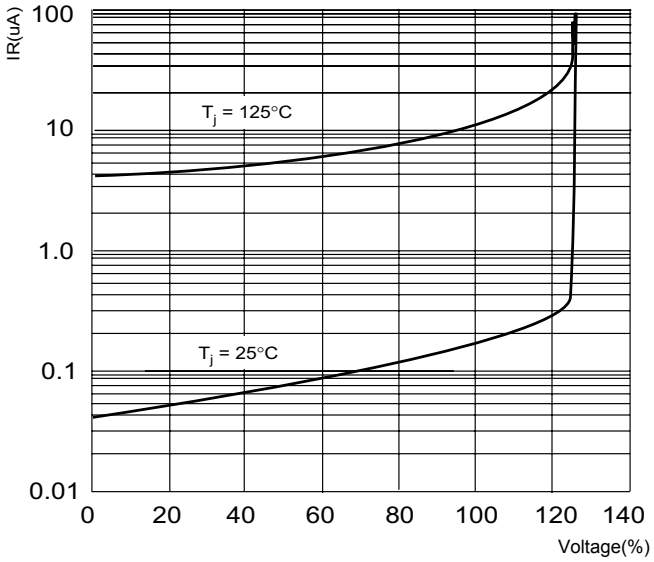
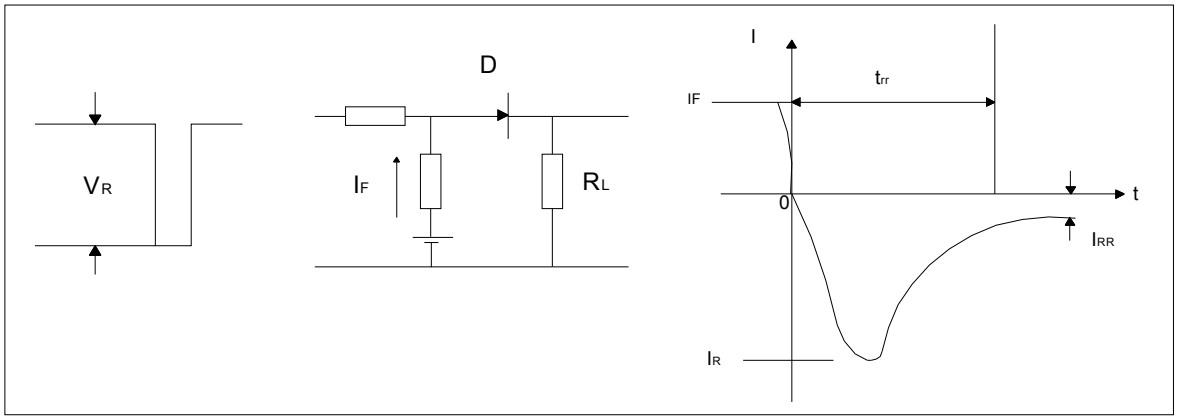
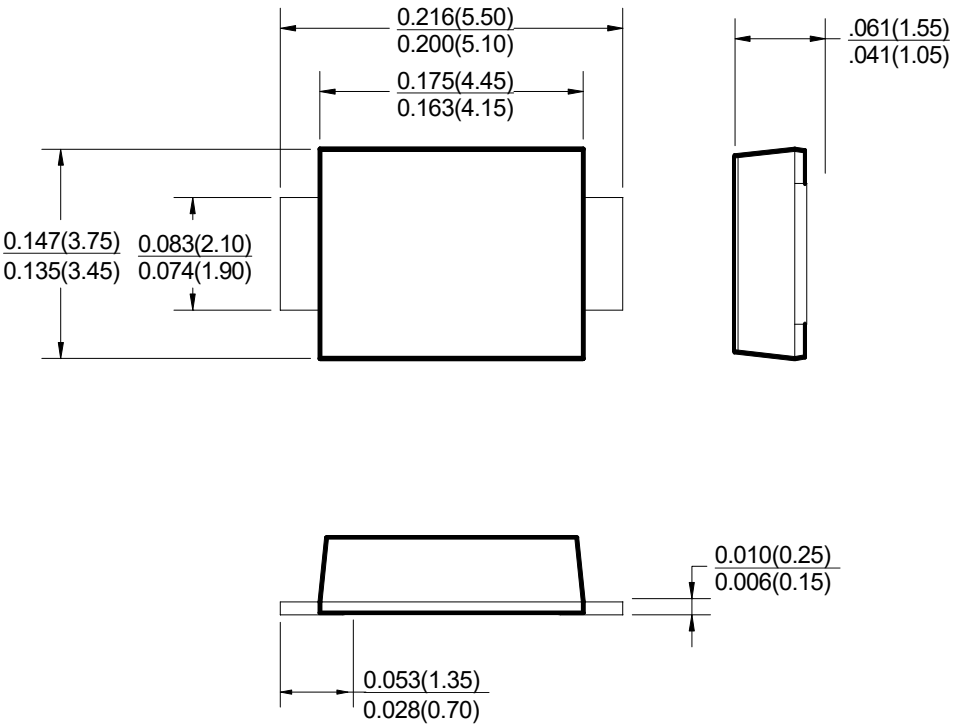


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time

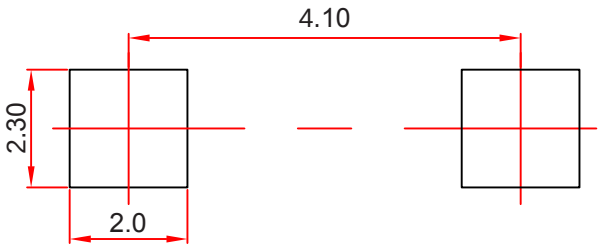


SMBF Package Outline Dimensions



Dimensions in inches and (millimeters)

SMBF Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.